

IN THE SPECIFICATION

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Please amend the paragraph beginning on page 1 line 27 as follows:

A1
CMP is a semiconductor wafer flattening and polishing process that combines the chemical removal of semiconductor layers such as insulators and metals with the mechanical buffering of a wafer surface. Typically, CMP is used to polish or flatten wafers after crystal ~~growing growth~~ during the wafer fabrication process, and to polish or flatten the profiles that build up in multilevel metal interconnection schemes.

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Please amend the paragraph beginning on page 6 line 8 as follows:

A2
The present subject matter provides chemical mechanical polishing (CMP) systems and methods in which a rotating polishing pad drum is used to polish a wafer held by a platen. The polishing pad drum operably contacts the wafer through a relative linear movement between the wafer and the rotating polishing pad drum. The linear motion is characterized as being perpendicular (albeit in a different plane) to the axis of rotation of the polishing drum, which significantly ~~increasing~~ increases the degree of long range planarization by reducing uniformity problems such as dishing and rounding of the features.

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Please amend the paragraph beginning on page 11 line 4 as follows:

A3
Figure 9 is a block diagram of one CMP system embodiment. According to this embodiment, the CMP system 900 includes a platen 902 and a polishing pad drum 904. The polishing pad drum 904 is adapted to be rotationally moved. A drum drive assembly 924 controls the rotational movement of the polishing pad drum 904. A controller 926 is coupled to and in communication with the drum drive assembly 924. According to various embodiments, the controller 926 and drum drive assembly ~~724~~ 924 cooperate to control the direction, speed and/or timing of the rotational movement of the polishing pad drum 904.